

# isc N-Channel MOSFET Transistor

# FCH041N65F

#### **FEATURES**

- Drain Current :  $I_D$ = 76A@  $T_C$ =25  $^{\circ}$ C
- Drain Source Voltage
  - : V<sub>DSS</sub>= 650V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 41 \text{m} \Omega \text{ (Max)} @ V_{GS} = 10 \text{V}$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **DESCRIPTION**

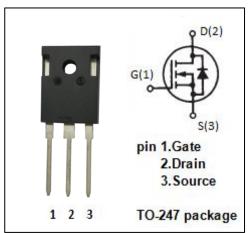
 motor drive, DC-DC converter, power switch and solenoid drive.

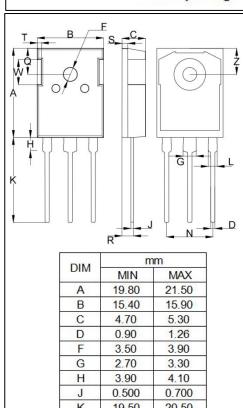
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	650	V
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	V
I <sub>D</sub>	Drain Current-Continuous	76	А
Ірм	Drain Current-Single Pluse	230	А
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	595	W
TJ	Max. Operating Junction Temperature	-55~150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.21	°C/W





В	15.40	15.90
С	4.70	5.30
D	0.90	1.26
F	3.50	3.90
G	2.70	3.30
Н	3.90	4.10
J	0.500	0.700
K	19.50	20.50
L	1.90	2.20
N	10.80	11.00
Q	6.00	6.30
R	2.90	3.30
S	1.80	2.20
T	2.15	2.35
W	4.90	5.10
Z	6.00	6.30

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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	650	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA	3	5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 38A	-	41	m Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0	-	±0.1	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0	-	10	uA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 38A; V <sub>GS</sub> = 0	-	1.2	V

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